1x2Mx32bit DRAM Card
2x2Mx32bit DRAM Card

MF18M1-J57ATXX
MF116M-J57ATXX

Connector Type

Two-piece 88-pin

DESCRIPTION

These DRAM CARDs are developed based on JEIDA DRAM CARD GUIDELINE Ver. 2.1.
These cards are made using industry standard 2 M × 8 Dynamic RAM and interface IC's in TSOP.

FEATURES

- Operating Voltage V_{CC}=3.3V±5%
- All inputs except $\overline{RAS}$ inputs are buffered.
- Standard card size : 54mm (W) ×85.6mm (L) ×3.3mm (T)
- 88pin 2 piece connector type.
- $\overline{RAS}$ only refresh mode, $\overline{CAS}$ before $\overline{RAS}$ refresh mode and Page mode functions are available.
- Extended refresh is available. (128ms/2048cycle)

APPLICATIONS

Main/expansion memory unit for Personal Computer. Laser-Printer, FAX etc.

PRODUCT LIST

Product No.	Item / Type name	Memory capacity	Data Bus width (bits)	Access time (t_{RAC}) (ns)	Connector type	Number of pins	Outline drawing
No. 1	MF18M1-J57ATXX	8 MB	32 (without parity)	70	Two-piece	88	88P-002
No. 2	MF116M-J57ATXX	16MB					

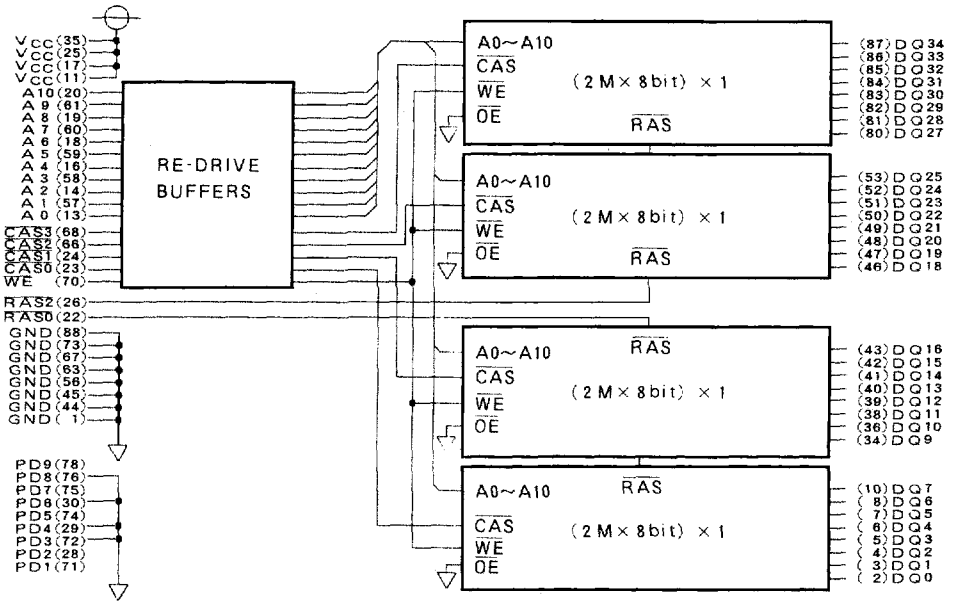
PIN ASSIGNMENT

Pin No.	Symbol	Function	Pin No.	Symbol	Function
1	GND	Ground	45	GND	Ground
2	DQ 0	Data I/O	46	DQ18	Data I/O
3	DQ 1		47	DQ19	
4	DQ 2		48	DQ20	
5	DQ 3		49	DQ21	
6	DQ 4		50	DQ22	
7	DQ 5		51	DQ23	
8	DQ 6		52	DQ24	
9	NC	No connection	53	DQ25	
10	DQ7	Data I/O	54	NC	No connection
11	Vcc	Power supply voltage	55	NC	No connection
12	NC	No connection	56	GND	Ground
13	A 0	Address input	57	A 1	Address input
14	A 2		58	A 3	
15	NC	No connection	59	A 5	
16	A 4	Address input	60	A 7	
17	Vcc	Power supply voltage	61	A 9	
18	A 6	Address input	62	NC	No connection
19	A 8		63	GND	Ground
20	A10		64	NC	No connection
21	NC	No connection	65	$\overline{RAS1}$	Row address strobe 1 (NC for No. 1)
22	$\overline{RAS0}$	Row address strobe 0	66	$\overline{CAS2}$	Column address strobe 2
23	$\overline{CAS0}$	Column address strobe 0	67	GND	Ground
24	$\overline{CAS1}$	Column address strobe 1	68	$\overline{CAS3}$	Column address strobe 3
25	Vcc	Power supply voltage	69	$\overline{RAS3}$	Row address strobe 3 (NC for No. 1)
26	$\overline{RAS2}$	Row address strobe 2	70	$\overline{WE}$	Write enable
27	NC	No connection	71	PD 1	Presence detect 1
28	PD 2	Presence detect 2	72	PD 3	Presence detect 3
29	PD 4	Presence detect 4	73	GND	Ground
30	PD 6	Presence detect 6	74	PD 5	Presence detect 5
31	NC	No connection	75	PD 7	Presence detect 7
32	NC		76	PD 8	Presence detect 8
33	NC	No connection	77	NC	No connection
34	DQ 9	Data I/O	78	PD 9	Presence detect 9
35	Vcc	Power supply voltage	79	NC	No connection
36	DQ10	Data I/O	80	DQ27	Data I/O
37	NC	No connection	81	DQ28	
38	DQ11	Data I/O	82	DQ29	
39	DQ12		83	DQ30	
40	DQ13		84	DQ31	
41	DQ14		85	DQ32	
42	DQ15		86	DQ33	
43	DQ16		87	DQ34	
44	GND	Ground	88	GND	Ground

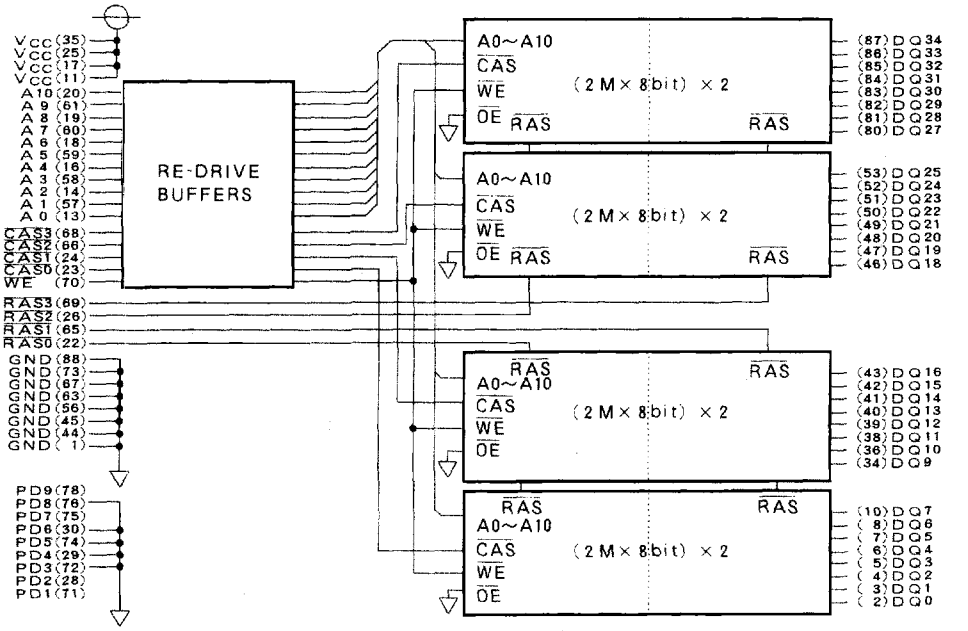
PD Pin Table

Product No.	PD 1	PD 2	PD 3	PD 4	PD 5	PD 6	PD 7	PD 8	PD 9
No. 1	NC	NC	GND	GND	NC	GND	NC	GND	NC
No. 2	NC	NC	GND	GND	GND	GND	NC	GND	NC

BLOCK DIAGRAM (No.1)



BLOCK DIAGRAM (No.2)



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FUNCTION TABLE

Operation	input					input/output		Refresh	Note
	$\overline{RAS}$	$\overline{CAS}$	$\overline{WE}$	Row Address	Column Address	input	output		
Read	ACT	ACT	NAC	APD	APD	OPN	VLD	YES	Page mode indentical
Early write	ACT	ACT	ACT	APD	APD	VLD	OPN	YES	
$\overline{RAS}$ only refresh	ACT	NAC	DNC	APD	DNC	DNC	OPN	YES	
$\overline{CAS}$ before $\overline{RAS}$ refresh	ACT	ACT	NAC	DNC	DNC	DNC	OPN	YES	
Self refresh	ACT	ACT	NAC	DNC	DNC	DNC	OPN	YES	
Standby	NAC	DNC	DNC	DNC	DNC	DNC	OPN	NO	

Note 1 : ACT : active, NAC : nonactive, DNC : don't care, VLD : valid, APD : applied, OPN : open
Don't be active the even and odd No. $\overline{RAS}$s at the same time. (Read/Early write cycle only)

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings		Unit
			No. 1	No. 2	
V_{CC}	Supply voltage	With respect to GND	−0.5～4.6		V
V_I	Input voltage		−0.5～4.6		V
V_O	Output voltage		−0.5～4.6		V
I_O	Output current		50		mA
P_d	Power dissipation	T_a=25℃	4	8	W
T_{opr}	Operating temperature		0～55		℃
T_{stg}	Storage temperature		−40～80		℃

RECOMMENDED OPERATING CONDITIONS (T_a= 0～55℃, unless otherwise noted): (Note 2)

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
V_{CC}	Supply voltage	3.135	3.3	3.465	V
GND	Supply voltage	0	0	0	V
V_{IH}	High input voltage	2.0		V_{CC}	V
V_{IL}	Low input voltage	0		0.8	V

Note 2 : With respect to GND

ELECTRICAL CHARACTERISTICS (T_a = 0 ~55℃, V_{CC}=3.3V± 5 %, GND= 0 V) : (Note 3)

Symbol	Parameter	Test condition	Limits					Unit
			Min.		Typ.	Max.		
			No. 1	No. 2		No. 1	No. 2	
V_{OH}	High output voltage	I_{OH} = − 2 mA	2.4			V_{CC}		V
V_{OL}	Low output voltage	I_{OL} = 2 mA	0			0.4		V
I_{OZ}	Off-stage output current	0 V ≦ V_{OUT} ≦ V_{CC}	−10	−20		10	20	μA
I_I	Input current	0 V ≦ V_{IN} ≦ V_{CC} Other input pins = 0 V	−20	−20		20	20	μA
$I_{CC1(AV)}$	Average supply current from V_{CC}, operating (Note 4, 5, 6)	$\overline{RAS}$, $\overline{CAS}$ cycling t_{RC} = t_{WC} = min, output open				450	460	mA
$I_{CC2(AV)}$	Supply current from V_{CC}, standby (Note 7)	$\overline{RAS}$ = $\overline{CAS}$ ≧ V_{CC} − 0.2V, other input pins ≧ V_{CC} − 0.2V or ≦ 0.2V, output open				3.0	5.0	mA
$I_{CC3(AV)}$	Average supply current from V_{CC}, refreshing (Note 4, 6)	$\overline{RAS}$ cycling, $\overline{CAS}$ = V_{IH} t_{RC} = min, output open				500	990	mA
$I_{CC4(AV)}$	Average supply current from V_{CC}, Page-Mode (Note 4, 5, 6)	$\overline{RAS}$ = V_{IL}, $\overline{CAS}$ cycling t_{RC} = min, output open				320	340	mA
$I_{CC6(AV)}$	Average supply current from V_{CC}, $\overline{CAS}$ before $\overline{RAS}$ refresh mode (Note 4, 6)	$\overline{CAS}$ before $\overline{RAS}$ refresh cycling t_{RC} = min, output open				490	970	mA
$I_{CC8(AV)}$	Average supply current from V_{CC}, Extended refresh mode (Note 7)	$\overline{CAS}$ before $\overline{RAS}$ refresh cycling WE ≧ V_{CC} − 0.2V other input pins ≧ V_{CC} − 0.2V or ≦ 0.2V, output open t_{RC} = 62.5 μs (t_{RAS} = t_{RAS}min ~ 1 μs)				7.0	9.0	mA
$I_{CC9(AV)}$	Average supply current from V_{CC}, Self refresh mode (Note 7)	$\overline{RAS}$ = $\overline{CAS}$ ≦ 0.2V, WE ≧ V_{CC} − 0.2V output open				7.0	9.0	mA

Note 3 : Current flowing into a CARD is positive, out is negative.

4 : I_{CC1} (AV), I_{CC3} (AV), I_{CC4} (AV) and I_{CC6} (AV) are dependent on cycle rate. Specified values are obtained at the fastest cycle rate.

5 : I_{CC1} (AV) and I_{CC4} (AV) are dependent on output loading. Specified values are obtained with the outputs open.

6 : Column Address can be changed once or less while $\overline{RAS}$ = V_{IL} and $\overline{CAS}$ = V_{IH}.

SWITCHING CHARACTERISTICS (T_a = 0 ~55℃, V_{CC} = 3.3V ± 5 %, GND = 0 V): (Note 7)

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{CAC}	Access time from $\overline{CAS}$ (Note 8, 9)		27	ns
t_{RAC}	Access time from $\overline{RAS}$ (Note 8, 10)		70	ns
t_{CAA}	Column Address access time (Note 8, 11)		42	ns
t_{OFF}	Output disable time after $\overline{CAS}$ high (Note12)	0	27	ns

Note 7 : An initial pause of 500 μsec is required after power-up followed by any 8 $\overline{RAS}$ or $\overline{RAS}$/$\overline{CAS}$ cycles before proper device operation is achieved. Note that $\overline{RAS}$ may be cycled during the initial pause. And any 8 $\overline{RAS}$ or $\overline{RAS}$/$\overline{CAS}$ cycles are required after prolonged periods of $\overline{RAS}$ inactivity before proper device operation is achieved.

8 : Measured with a load circuit equivalent to 2 TTL loads and 100pF.

9 : Assume that $t_{RCD} \geqq t_{RCD(max)}$ and $t_{ASC} \geqq t_{ASC(max)}$.

10 : Assume that $t_{RCD} \leqq t_{RCD(max)}$ and $t_{RAD} \leqq t_{RAD(max)}$.

11 : Assume that $t_{RAD} \geqq t_{RAD(max)}$ and $t_{ASC} \leqq t_{ASC(max)}$.

12 : $t_{OFF(max)}$ define the time at which the output achieves the high impedance state (No. 1 : | I out | ≦10 μA, No. 2 : | I out | ≦20 μA) and are not reference to $V_{OH(min)}$ or $V_{OL(max)}$.

TIMING REQUIREMENTS (T_a = 0 ~55℃, V_{CC} = 3.3V ± 5 %, GND = 0 V) : (Note 13, 14)

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{REF}	Refresh cycle time		32	ms
t_{REF}	Refresh cycle time ($\overline{CAS}$ before $\overline{RAS}$ refresh cycling)		128	ms
t_{RP}	$\overline{RAS}$ high pulse width	50		ns
t_{RCD}	Delay time, $\overline{RAS}$ low to $\overline{CAS}$ low (Note15)	20	43	ns
t_{CRP}	Delay time, $\overline{CAS}$ high to $\overline{RAS}$ low (Note16)	17		ns
t_{RPC}	Precharge to $\overline{CAS}$ active time.	0		ns
t_{CPN}	$\overline{CAS}$ high pulse width	10		ns
t_{RAD}	Column address delay time from $\overline{RAS}$ low (Note 17)	17	28	ns
t_{ASR}	Row address setup time before $\overline{RAS}$ low	10		ns
t_{ASC}	Column address setup time before $\overline{CAS}$ low (Note18)	5	10	ns
t_{RAH}	Row address hold time after $\overline{RAS}$ low	10		ns
t_{CAH}	Column address hold time after $\overline{CAS}$ low	15		ns
t_T	Transition time (Note19)	3	50	ns

Note 13 : The timing requirements are assumed t_T = 5 ns.

14 : V_{IH}(min) and V_{IL}(max) are reference levels for measuring timing of input signals.

15 : t_{RCD}(max) is specified as a reference point only.
If $t_{RCD} \geqq t_{RCD}$(max), access time is defined as t_{CAC} and t_{CAA}.

16 : t_{CRP} requirement is applicable for all $\overline{RAS}$/$\overline{CAS}$ cycles.

17 : t_{RAD}(max) is specified as a reference point only.
If $t_{RAD} \geqq t_{RAD}$(max) and $t_{ASC} \leqq t_{ASC}$(max), access time is assumed by t_{CAA} for read cycle.

18 : t_{ASC}(max) is specified as a reference point only of address access time.

19 : t_T is measured between V_{IH}(min) and V_{IL}(max).

Read and Refresh Cycles

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{RC}	Read cycle time	130		ns
t_{RAS}	$\overline{RAS}$ low pulse width	70	10000	ns
t_{CAS}	$\overline{CAS}$ low pulse width	20	10000	ns
t_{CSH}	$\overline{CAS}$ hold time after $\overline{RAS}$ low	70		ns
t_{RSH}	$\overline{RAS}$ hold time after $\overline{CAS}$ low	27		ns
t_{RSC}	Read setup time before $\overline{CAS}$ low	5		ns
t_{RCH}	Read hold time after $\overline{CAS}$ high	0		ns
t_{RRH}	Read hold time after $\overline{RAS}$ high	10		ns

Write Cycle (Early Write)

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{WC}	Write cycle time	130		ns
t_{RAS}	$\overline{RAS}$ low pulse width	70	10000	ns
t_{CAS}	$\overline{CAS}$ low pulse width	20	10000	ns
t_{CSH}	$\overline{CAS}$ hold time after $\overline{RAS}$ low	70		ns
t_{RSH}	$\overline{RAS}$ hold time after $\overline{CAS}$ low	27		ns
t_{WCS}	Write setup time before $\overline{CAS}$ low	5		ns
t_{WCH}	Write hold time after $\overline{CAS}$ low	15		ns
t_{DS}	Data setup time	10		ns
t_{DH}	Data hold time after $\overline{CAS}$ low	22		ns

Page Mode Cycle (Read, Early Write)

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{PC}	Read, Write cycle time	55		ns
t_{CP}	$\overline{CAS}$ high pulse width	10		ns
t_{RAS}	$\overline{RAS}$ low pulse width (Note 20)	125	100000	ns

Note 20 : $t_{RAS}(min)$ is specified by the following formula as two cycles of $\overline{CAS}$ input are executed.
$t_{RAS}(min) = t_{CSH}(min) + t_{PC}(min)$.

$\overline{CAS}$ before $\overline{RAS}$ Refresh Cycle (Note 21)

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{CSR}	$\overline{CAS}$ setup time for $\overline{CAS}$ before $\overline{RAS}$ refresh	20		ns
t_{CHR}	$\overline{CAS}$ hold time for $\overline{CAS}$ before $\overline{RAS}$ refresh	15		ns

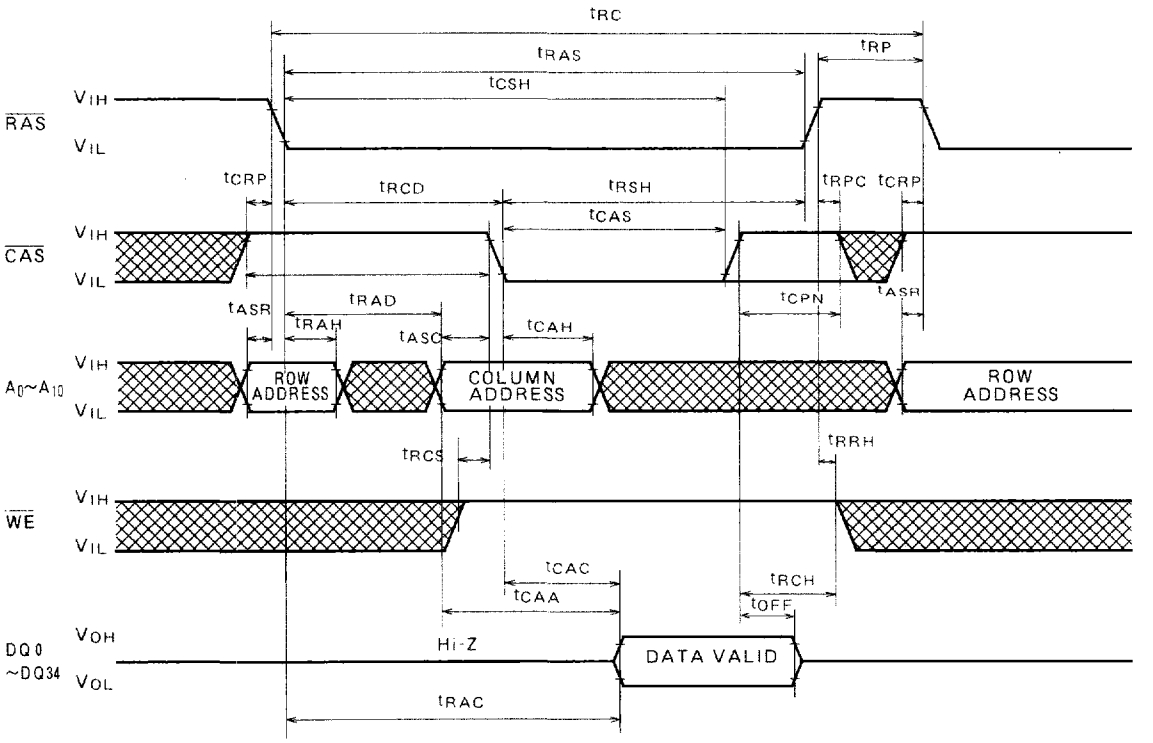
Note 21 : Eight or more $\overline{CAS}$ before $\overline{RAS}$ cycles are necessary for proper operation of $\overline{CAS}$ before $\overline{RAS}$ refresh mode.

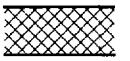
Self Refresh Cycle

Symbol	Parameter	Limits		Unit
		Min.	Max.	
t_{RASS}	$\overline{RAS}$ low pulse width	100		μs
t_{RPS}	$\overline{CAS}$ high pulse width	130		ns
t_{CHS}	$\overline{RAS}$ hold time after $\overline{RAS}$ high	−50		ns

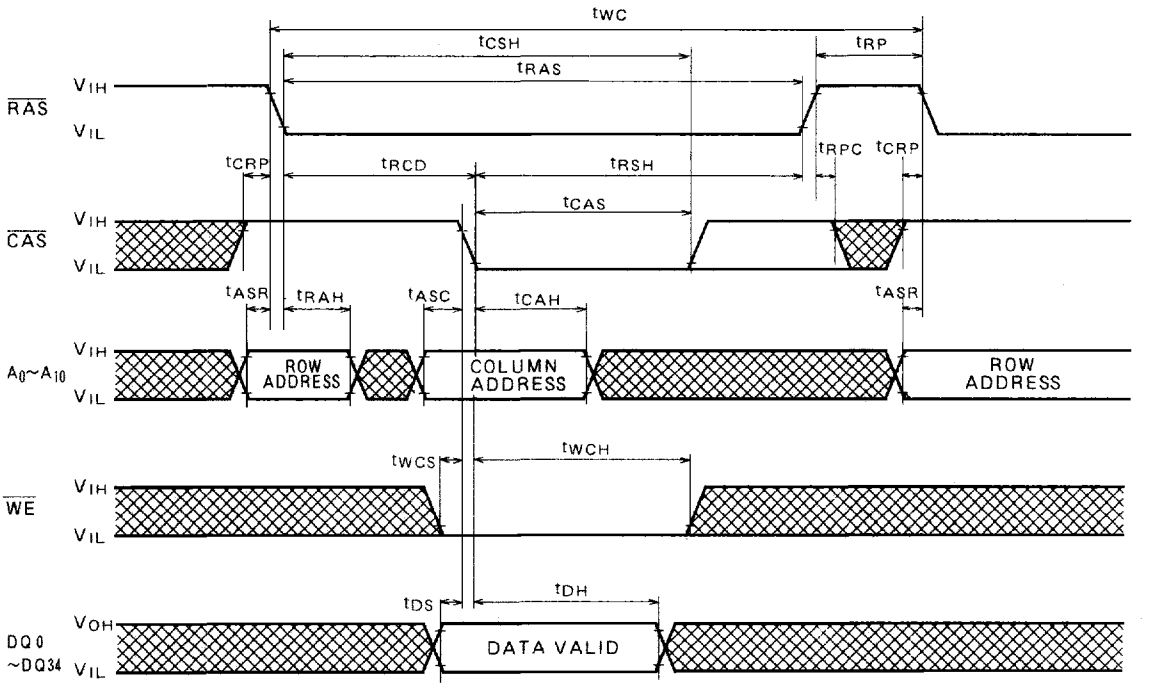
TIMING DIAGRAMS (Note 22)

Read Cycle

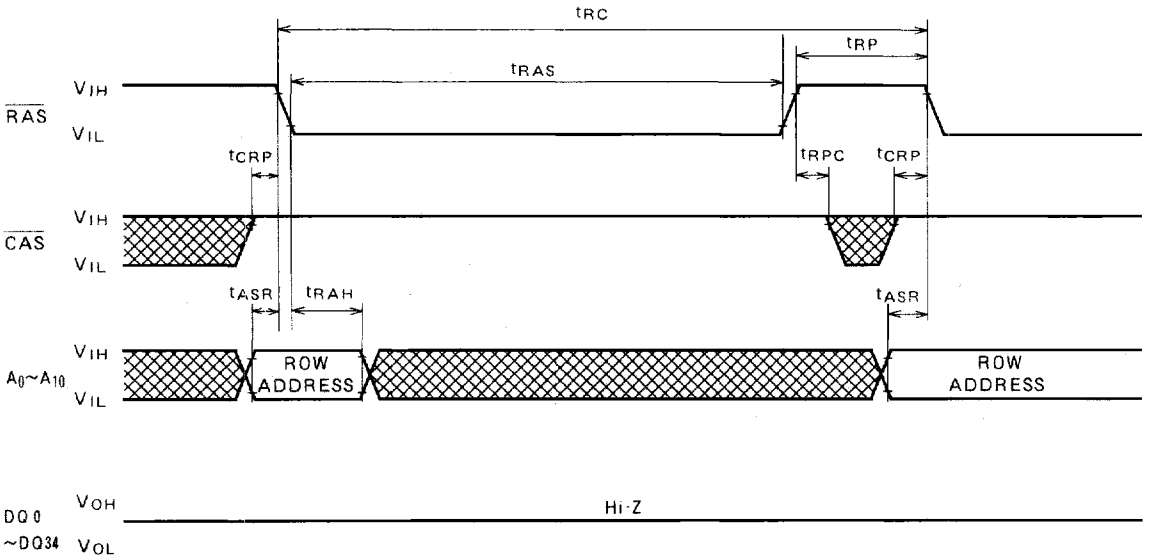


Note 22 :  Indicates the don't care input.

Early Write Cycle

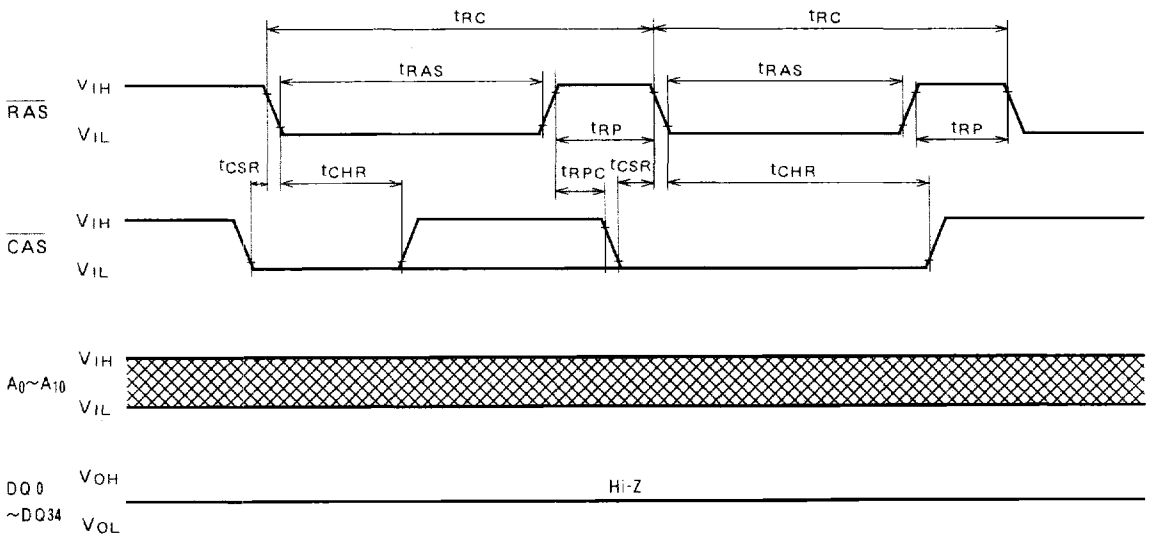


$\overline{RAS}$ only Refresh Cycle (Note 23)



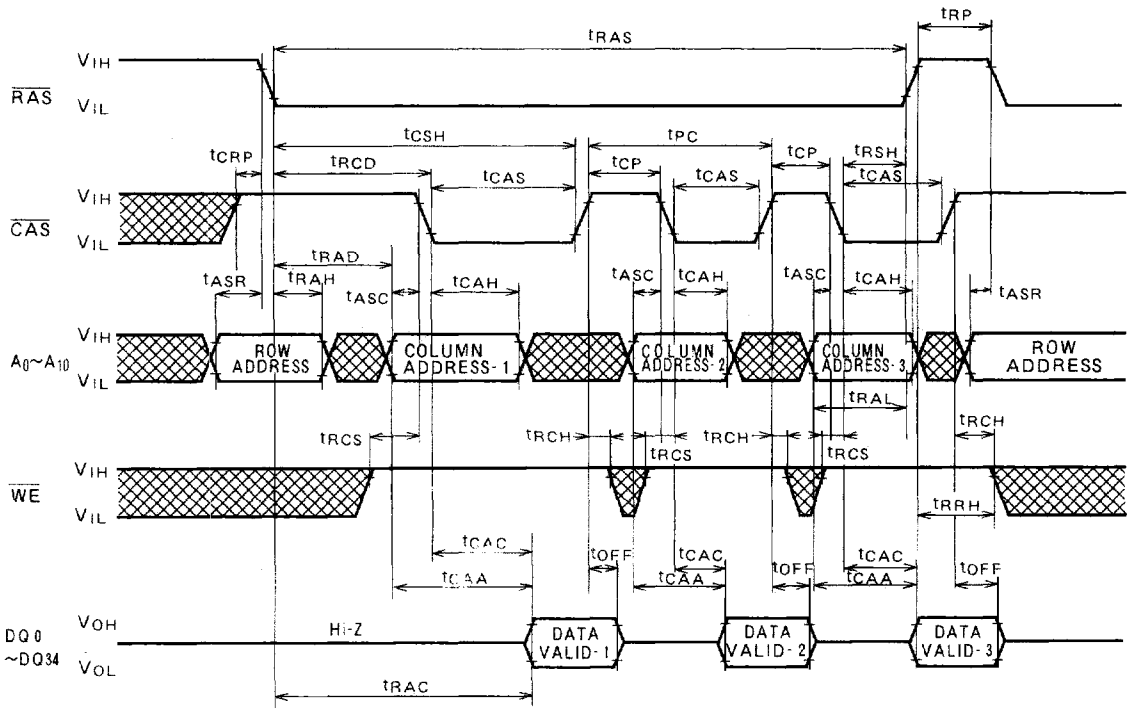
Note 23 : $\overline{WE}$ = don' t care.

$\overline{CAS}$ before $\overline{RAS}$ Refresh Cycle (Note 24)

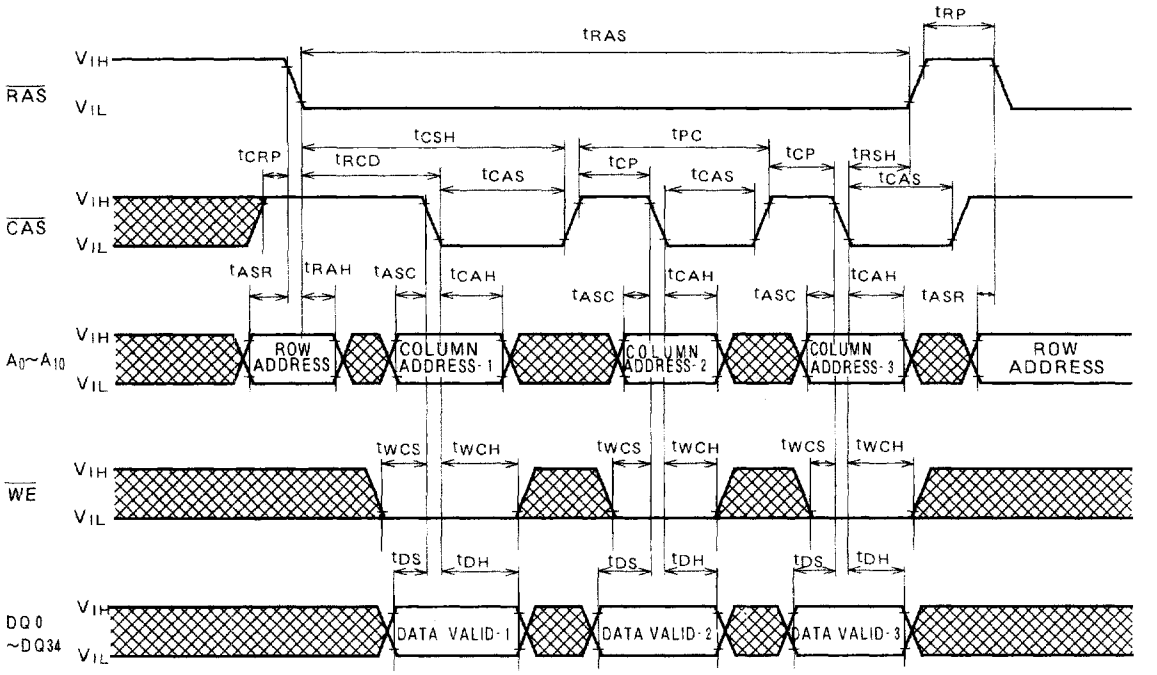


Note 24 : $\overline{WE}$ = V_{IH}

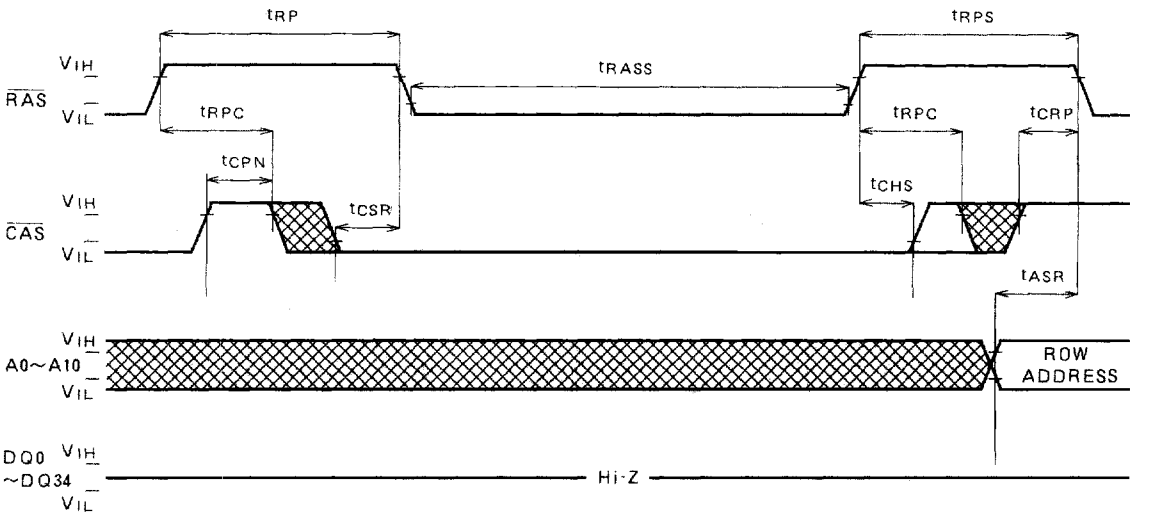
Page-Mode Read Cycle



Page-Mode Early Write Cycle



Self Refresh Cycle (Note 25, 26)

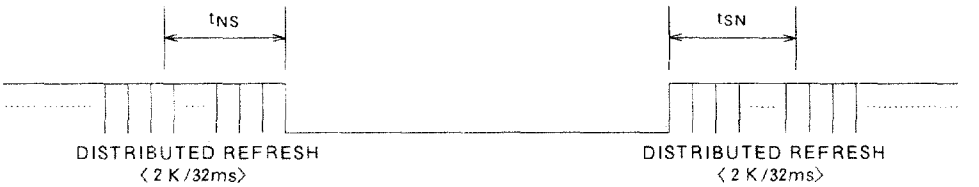


Note 25 : $\overline{WE} = V_{IH}$

Note 26 : SELF REFRESH ENTRY & EXIT CONDITIONS

(1)In case of distributed refresh

The last/first full refresh cycles (2 K) must be made within t_{NS}/t_{SN} before/after self refresh, on the condition of $t_{NS} \leqq 32ms$ and $t_{SN} \leqq 32ms$.



(2)In case of burst refresh

The last/first full refresh cycles (2 K) must be made within t_{NS}/t_{SN} before/after self refresh, on the condition of $t_{NS}+t_{SN} \leqq 32ms$.